风光欣技术资料

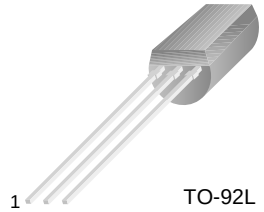
T5610

—PNP silicon —

■■**APPLICATION**: Audio Amplifier and Switching Applications.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



TO-92L

1. Emitter 2. Collector 3. Base

■■**ELECTRICAL CHARACTERISTICS（Ta=25℃）**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	80		360		V_{CE}= -2V，Ic= -500mA
Collector Cut-off Current	I_{CBO}			-1	μA	V_{CB}= -20V，I_E=0
Emitter Cut-off Current	I_{EBO}			-1	μA	V_{EB}= -4V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	-25			V	Ic= -0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-20			V	Ic= -1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -0.1mA，Ic=0
Base-Emitter Voltage	V_{BE}			-0.8	V	V_{CE}= -2V，Ic= -500mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.2	-0.5	V	Ic= -800mA，I_B= -80mA
Gain bandwidth product	f_T		350		MHz	Ic= -500mA，V_{CE}= -2V
Common Base Output Capacitance	Cob		38		PF	V_{CB}= -10V，I_E=0，f＝1MHz

■■hFE **Classification And Marking**

Classification	A	B	C	D
h_{FE}	80～120	85～170	120～240	180～360